

RB501V-40 SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type
- High reliability

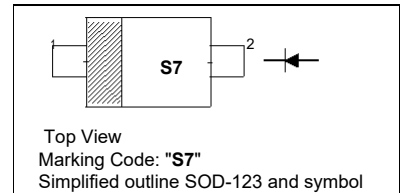
Applications

- Low current rectification

MARKING:S7

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	0.1	A
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 10\text{ mA}$	V_F	-	0.55	V
	V_F	-	0.34	V
Reverse Current at $V_R = 10\text{ V}$	I_R	-	30	μA
Capacitance Between Terminals at $V_R = 10\text{ V}$, $f = 1\text{ MHz}$	C_T	6	-	pF

Note: ESD sensitive product handling required.

Typical Characteristics

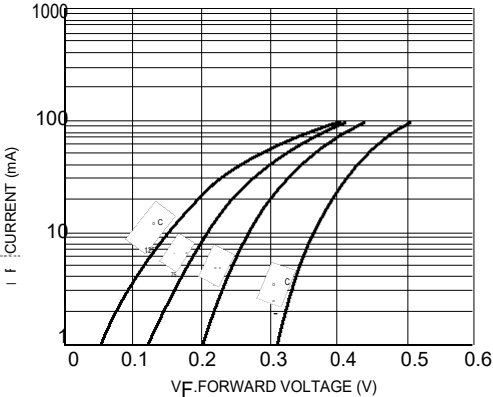


Figure1 Forward characteristics

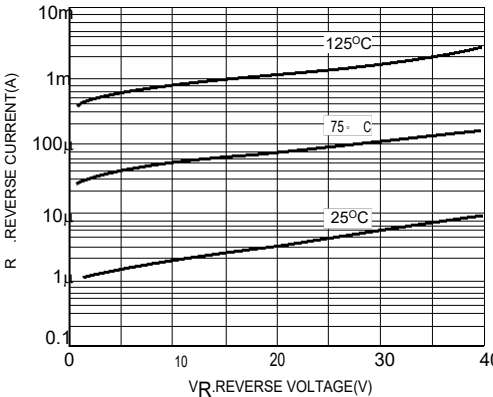


Fig e2 Reve se characteristics

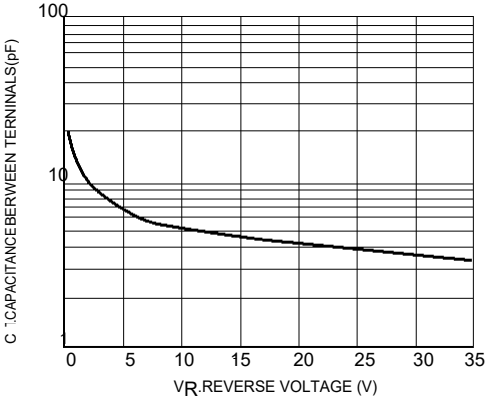


Figure3 Capacitance between terminals characteristics

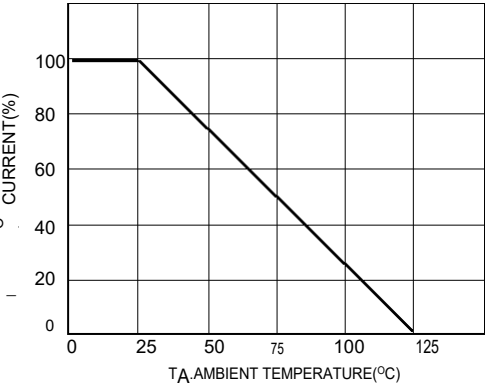


Figure4 Derating curve(mounting on glass epoxy PCBs)

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123

